# **UNR91A4G**

### Silicon PNP epitaxial planar type

#### For digital circuits

#### ■ Features

- Optimum for high-density mounting and downsizing of the equipment
- Contribute to low power consumption

#### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V	
Collector current	$I_{C}$	-80	mA	
Total power dissipation	P <sub>T</sub>	125	mW	
Junction temperature	$T_j$	125	°C	
Storage temperature	T <sub>stg</sub>	-55 to +125	°C	

#### ■ Package

- Code
- SSMini3-F3
- Pin Name
  - 1: Base
  - 2: Emitter
  - 3: Collector

### ■ Marking Symbol: CK

#### ■ Internal Connection

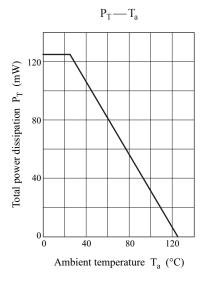
$$R_1$$
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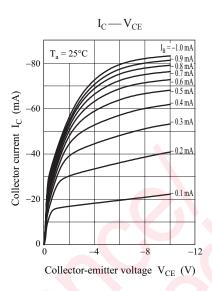
### ■ Electrical Characteristics $T_a = 25$ °C±3°C

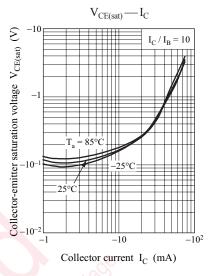
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_{B} = 0$			- 0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = -6 \text{ V}, I_C = 0$			- 0.2	mA
Forward current transfer ratio	$h_{FE}$	$V_{CE} = -10 \text{ V}, I_{C} = -5 \text{ mA}$	80			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -10 \text{ mA}, I_B = -0.3 \text{ mA}$			- 0.25	V
Output voltage high-level	V <sub>OH</sub>	$V_{CC} = -5 \text{ V}, V_{B} = -0.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$	-4.9			V
Output voltage low-level	V <sub>OL</sub>	$V_{CC} = -5 \text{ V}, V_{B} = -2.5 \text{ V}, R_{L} = 1 \text{ k}\Omega$			- 0.2	V
Input resistance	$R_1$		-30%	10	+30%	kΩ
Resistance ratio	$R_1/R_2$		0.17	0.21	0.25	
Transition frequency	$f_T$	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$		80		MHz

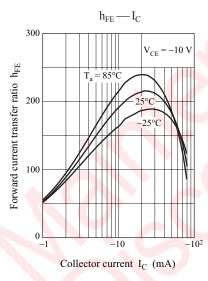
 $Note) \quad \text{Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS~C~7030~measuring~methods~for~transistors.}$ 

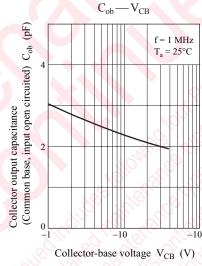
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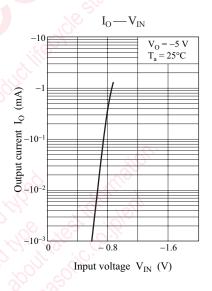


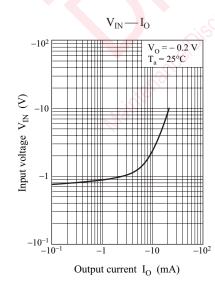








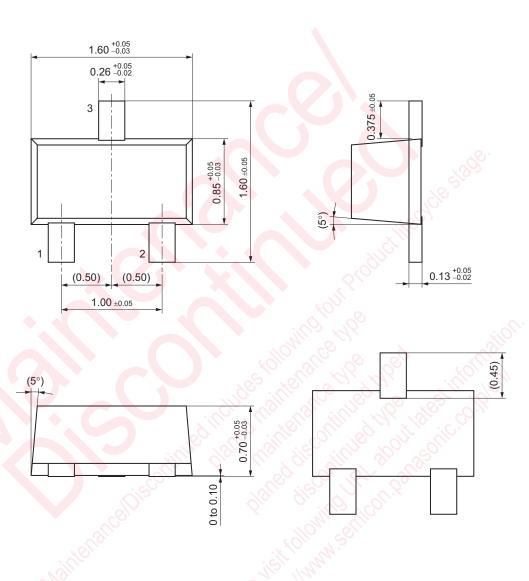




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Panasonic UNR91A4G

SSMini3-F3 Unit: mm



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